

Contributors to This Issue

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CLAYTON B. BROWN, B.S.E.E., 1952, Polytechnic Institute of Brooklyn; Bell Telephone Laboratories, 1937—. Mr. Brown has been engaged in the development of central office switching apparatus and solderless wrapped connections. He is currently a supervisor at the Columbus Laboratory responsible for the development of crossbar switches and wire spring and miscellaneous relays.

EARL F. BROWN, RCA Institutes Inc., 1955; Bell Telephone Laboratories, 1955—. Since joining Bell Telephone Laboratories Mr. Brown has been engaged in means to improve the quality of television pictures, subjective evaluation of television pictures, and means to compress the bandwidth of television signals.

E. A. J. MARCATILI, Aeronautical Engineer, 1947, and E.E., 1948, University of Córdoba (Argentina); research staff, University of Córdoba, 1947-54; Bell Telephone Laboratories, 1954—. Mr. Marcatili has been engaged in the theory and design of filters in multimode waveguides and in wave-guide systems research. More recently he has concentrated in the study of optical transmission media. Fellow, IEEE.

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DONALD K. WILSON, B.S., 1950 and M.S., 1951, Pennsylvania State University; Ph.D., 1963, Rutgers University; Bell Telephone Laboratories, 1951-1954, 1956—. Mr. Wilson has worked on alloyed and diffused silicon diodes and transistors, measurements of bulk semicon-

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